

09/694353

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	145	438/142	USPAT; EPO; JPO	2002/01/07 08:51
2	BRS	L2	0	semiconductor adj side adj wall adj fin	USPAT; EPO; JPO	2002/01/07 08:53
3	BRS	L3	103	side adj wall adj fin	USPAT; EPO; JPO	2002/01/07 08:54
4	BRS	L4	575	wall adj fin	USPAT; EPO; JPO	2002/01/07 08:54
5	BRS	L5 ✓	10	semiconductor adj fin	USPAT; EPO; JPO	2002/01/07 08:55
6	BRS	L6	56541	fet	USPAT; EPO; JPO	2002/01/07 08:55
7	BRS	L7 ✓	6	double adj gated adj field adj effect adj transistor	USPAT; EPO; JPO	2002/01/07 08:56
8	BRS	L8	401	SOI adj MOSFET	USPAT; EPO; JPO	2002/01/07 08:56
9	BRS	L9 ✓	33	damascene adj gate	USPAT; EPO; JPO	2002/01/07 08:57
10	BRS	L10	103	3 and 4	USPAT; EPO; JPO	2002/01/07 08:57
11	BRS	L11	0	1 and 3	USPAT; EPO; JPO	2002/01/07 08:58
12	BRS	L12 ✓	26	1 and 6	USPAT; EPO; JPO	2002/01/07 08:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	0	3 and 6	USPAT; EPO; JPO	2002/01/07 08:58
14	BRS	L14	0	3 and 8	USPAT; EPO; JPO	2002/01/07 08:58
15	BRS	L15	146	6 and 8	USPAT; EPO; JPO	2002/01/07 08:58
16	BRS	L16 ✓	1	1 and 6 and 8 <i>6,281,593</i>	USPAT; EPO; JPO	2002/01/07 08:59
17	BRS	L17	0	4 and 6 and 8	USPAT; EPO; JPO	2002/01/07 08:59

L15

~~6,326,247~~
~~*6,323,082~~
~~-6,303,479~~
~~-6,232,163~~
~~-6,159,778~~

~~-6,063,686~~
~~*5,981,318~~
~~*5,780,329~~
~~*5,773,328~~
~~*5,736,437~~

L3

*5,661,061

L5
X

L7

~~-5,349,228~~
~~-5,273,921~~

L9

~~-6,333,247~~
~~-6,333,229~~
~~-6,329,256~~
~~*6,291,278~~
~~-6,271,132~~
~~*6,258,679~~

L12

~~-6,323,103~~
~~-6,284,637~~
~~*6,165,822~~
~~*6,114,195~~
~~*5,950,076~~
~~5,944,970~~